H7P0601DL, H7P0601DS

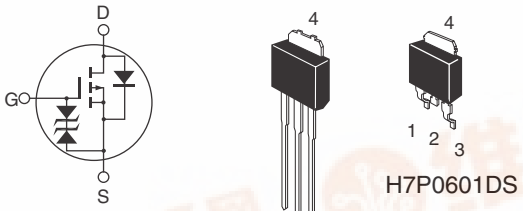
Silicon P Channel MOS FET
High Speed Power Switching

REJ03G0044-0100Z
Rev.1.00
Aug.05.2003

Features

- Low on-resistance
  $R_{DS(on)}$ = 40 mΩ typ.
- Low drive current
- 4.5 V gate drive device can driven from 5 V source

Outline



DPAK-2

H7P0601DL

DPAK-S

H7P0601DS

1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	–60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	–20	A
Drain peak current	I_D (pulse)[Note1]	–80	A
Body-drain diode reverse drain current	I_{DR}	–20	A
Avalanche current	I_{AP} [Note3]	–12	A
Avalanche energy	E_{AR} [Note3]	12.3	mJ
Channel dissipation	Pch [Note2]	25	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg ≥ 50 Ω

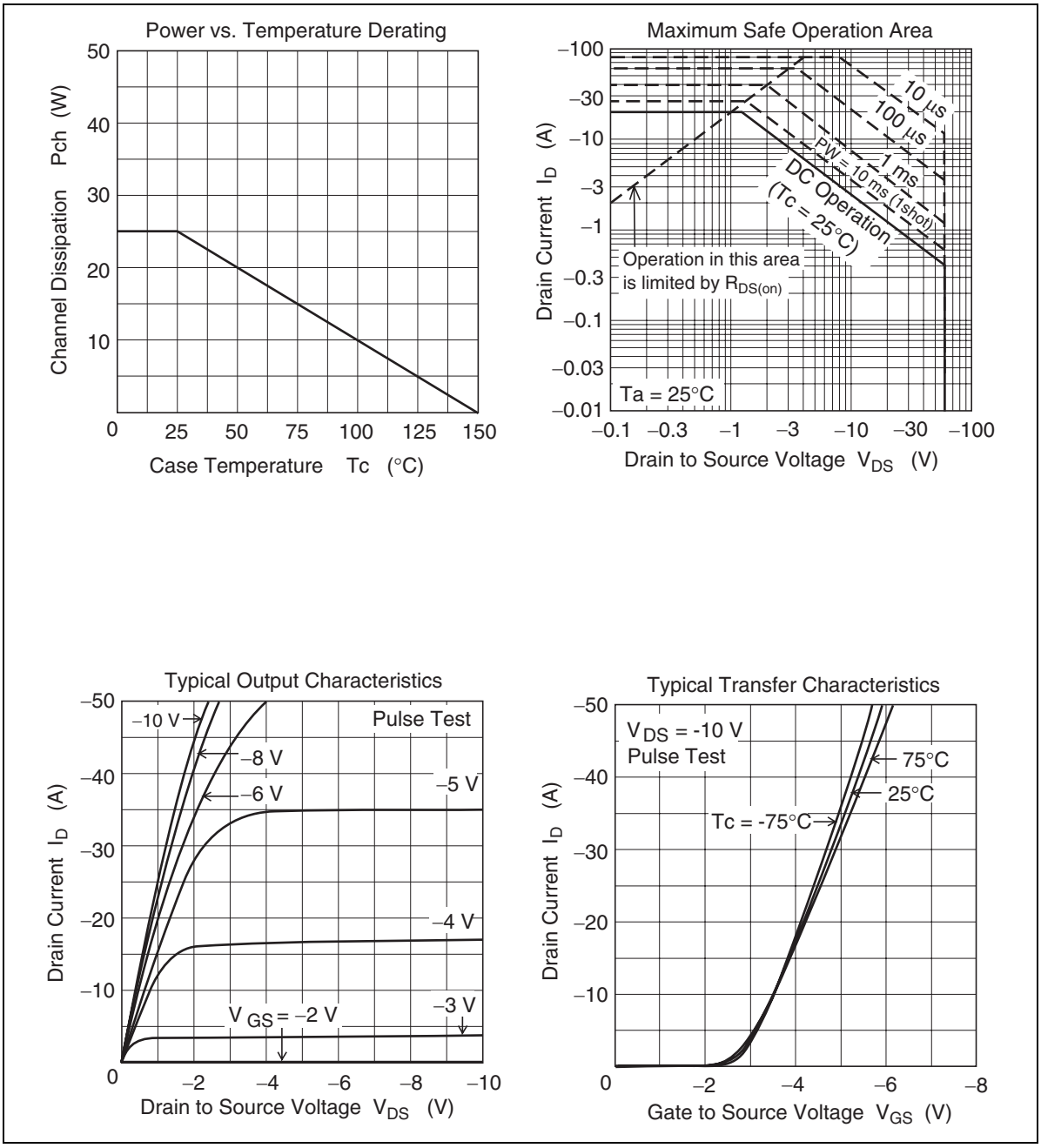
Electrical Characteristics

(Ta = 25°C)

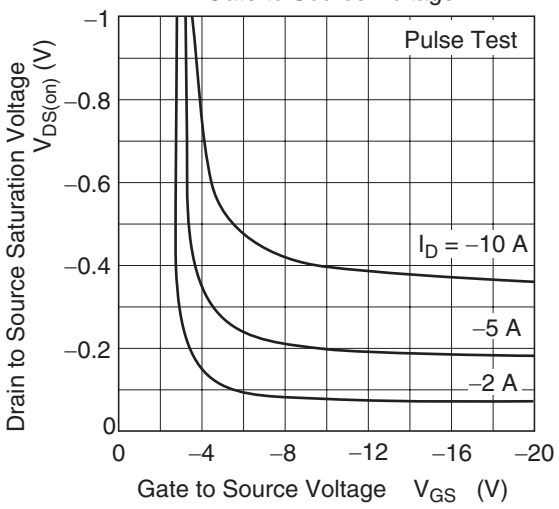
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	–60	—	—	V	I_D = –10 mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	µA	V_{GS} = ±16 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	–10	µA	V_{DS} = –60 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	–1.0	—	–2.5	V	I_D = –1 mA, V_{DS} = –10 V
Static drain to source on state resistance	$R_{DS(on)}$	—	40	50	mΩ	I_D = –10 A, V_{GS} = –10 V Note1
		—	60	85	mΩ	I_D = –5 A, V_{GS} = –4.5 V Note1
Forward transfer admittance	$\|y_{fs}\|$	7.2	12	—	S	I_D = –10 A, V_{DS} = –10 V Note1
Input capacitance	Ciss	—	2200	—	pF	V_{DS} = –10 V V_{GS} = 0 f = 1 MHz
Output capacitance	Coss	—	220	—	pF	
Reverse transfer capacitance	Crss	—	130	—	pF	
Total gate charge	Qg	—	37	—	nC	V_{DD} = –25 V V_{GS} = –10 V I_D = –20 A
Gate to source charge	Qgs	—	6.5	—	nC	
Gate to drain charge	Qgd	—	8	—	nC	
Turn-on delay time	$t_{d(on)}$	—	25	—	ns	V_{GS} = –10 V, I_D = –10 A R_L = 3.0 Ω Rg = 4.7 Ω
Rise time	t_r	—	85	—	ns	
Turn-off delay time	$t_{d(off)}$	—	70	—	ns	
Fall time	t_f	—	15	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.95	—	V	I_F = –20 A, V_{GS} = 0
Body-drain diode reverse recovery time	t_{rr}	—	30	—	ns	I_F = –20 A, V_{GS} = 0 diF/dt = 100 A/µs

Note: 1. Pulse test

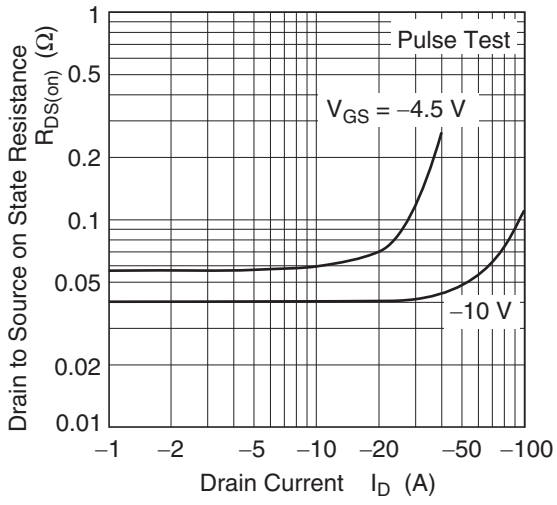
Main Characteristics



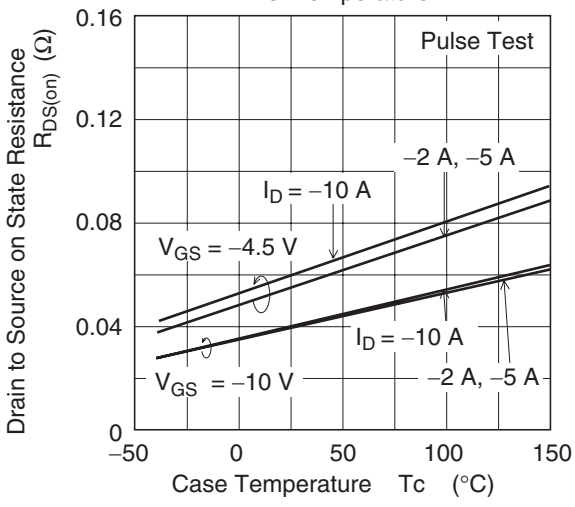
Drain to Source Saturation Voltage vs. Gate to Source Voltage



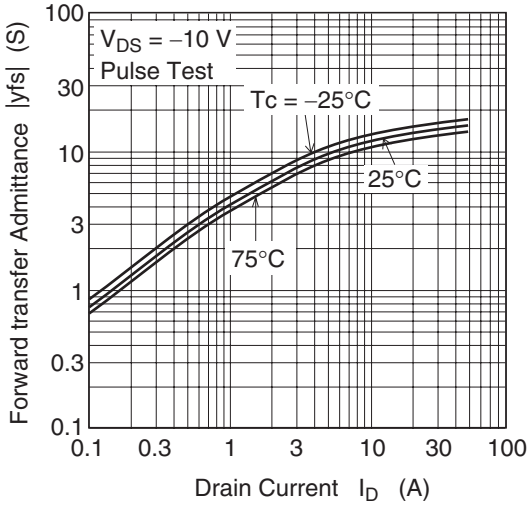
Static Drain to Source on State Resistance vs. Drain Current



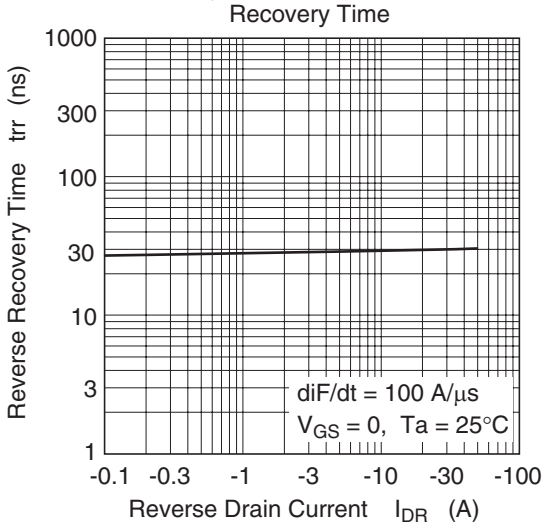
Static Drain to Source on State Resistance vs. Temperature



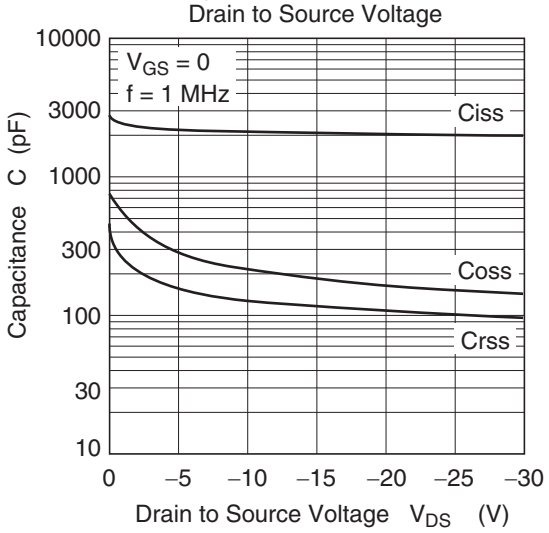
Forward Transfer Admittance vs. Drain Current



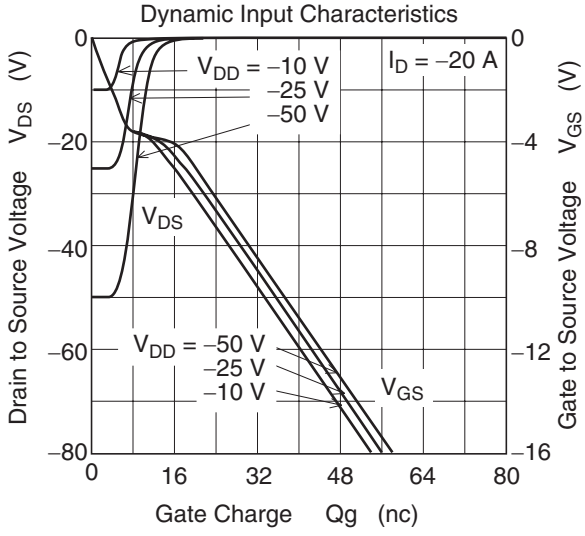
Body-Drain Diode Reverse Recovery Time



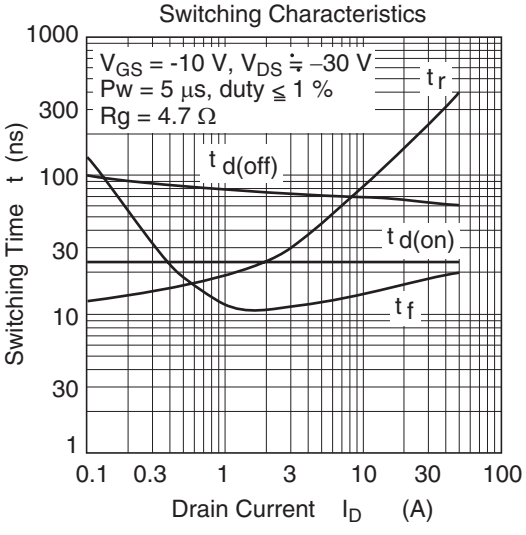
Typical Capacitance vs. Drain to Source Voltage



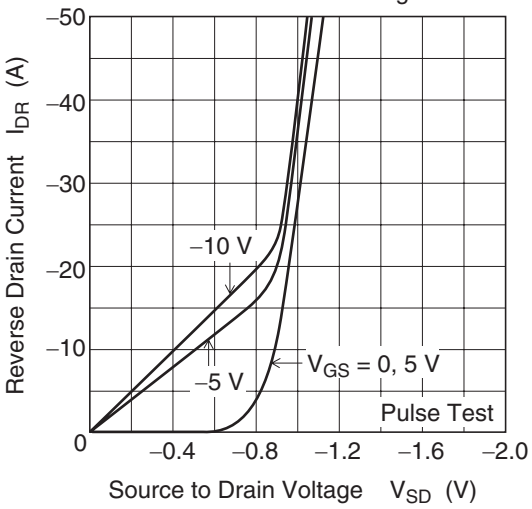
Dynamic Input Characteristics



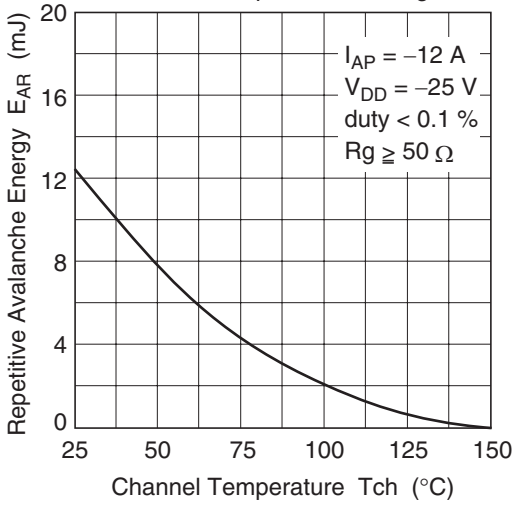
Switching Characteristics



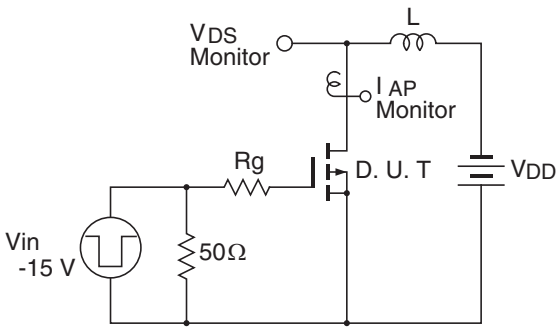
Reverse Drain Current vs. Source to Drain Voltage



Maximum Avalanche Energy vs. Channel Temperature Drating

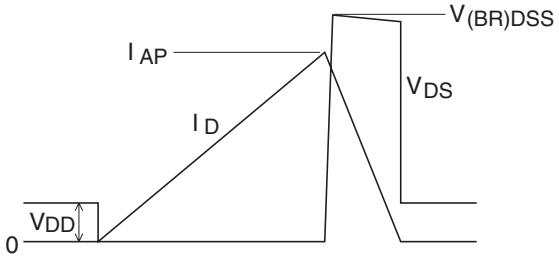


Avalanche Test Circuit

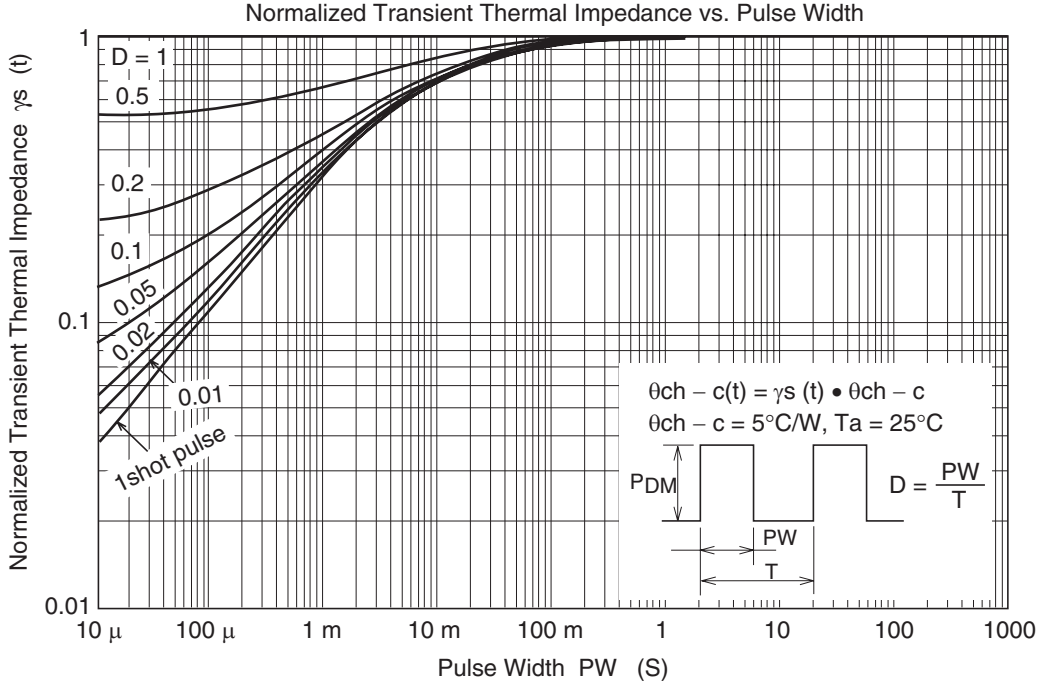


Avalanche Waveform

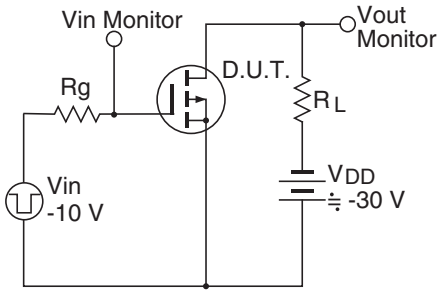
$$E_{AR} = \frac{1}{2} L \bullet I_{AP}^2 \bullet \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



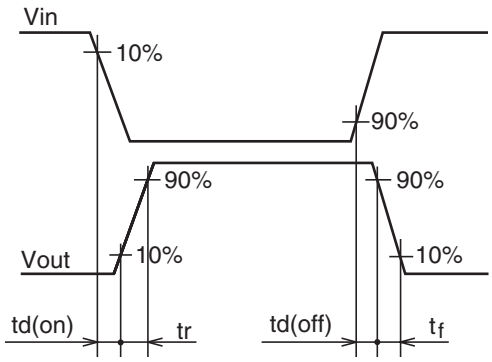
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit



Switching Time Waveform

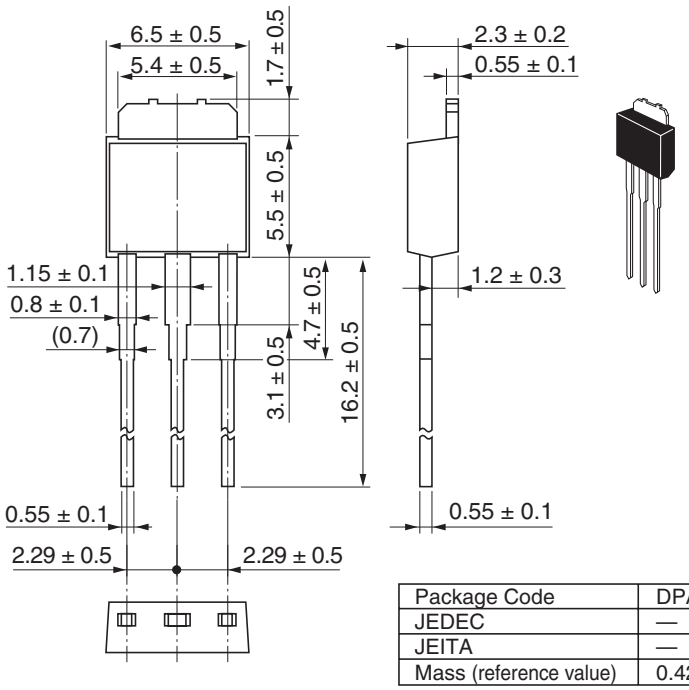


Package Dimensions

• H7P0601DL

As of January, 2003

Unit: mm

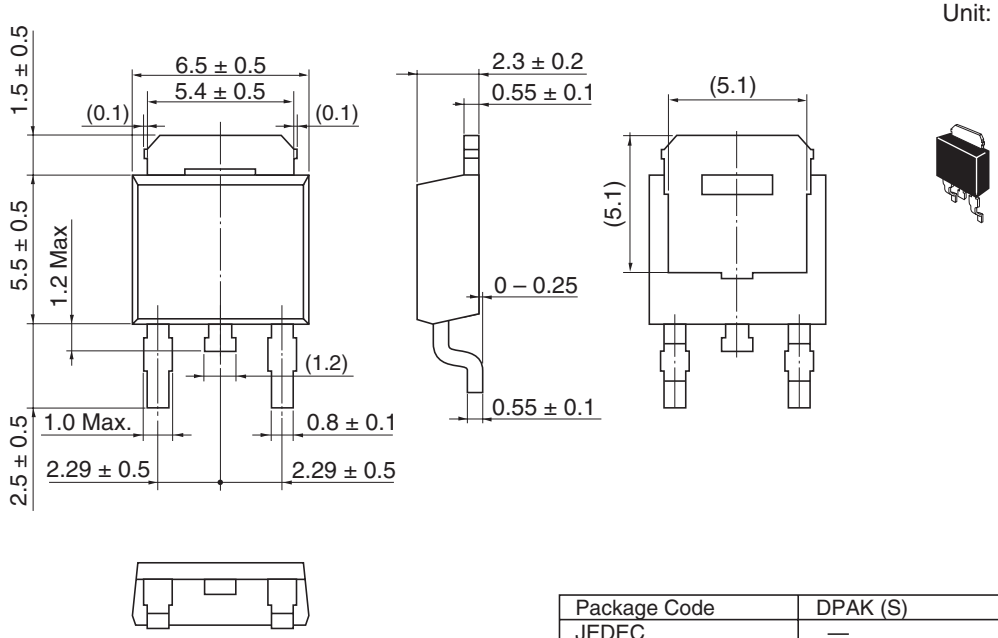


Package Code	DPAK (L)-(2)
JEDEC	—
JEITA	—
Mass (reference value)	0.42 g

• H7P0601DS

As of January, 2003

Unit: mm



Package Code	DPAK (S)
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.28 g

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